NPN Epitaxial Planar Type Silicon Transistor



2SC3785

Driver Applications

Applications

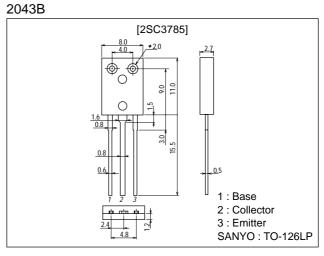
• Suitable for use in switching of L load (motor drivers, printer hammer drivers, relay drivers).

Features

- · High DC current gain.
- · Wide ASO.
- \cdot On-chip Zener diode of 60±10V between collector and base.
- · Uniformity in collector-to-base breakdown voltage.
- · Large inductive load handling capability.

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		50*	V
Collector-to-Emitter Voltage	VCEO		50*	V
Emitter-to-Base Voltage	VEBO		6	V
Collector Current	۱ _C		2	A
Collector Current (Pulse)	I _{CP}		4	A
Collector Dissipation	De		1.2	w
	PC	Tc=25°C	20	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

* : On-chip Zener diode (60±10V)

Electrical Characteristics at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =40V, I _E =0			10	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =5V, I _C =0			2	mA
DC Current Gain	hFE	V _{CE} =5V, I _C =1A	1000	4000		
Gain-Bandwidth Product	fT	V _{CE} =5V, I _C =1A		180		MHz
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =1A, I _B =4mA		1.0	1.5	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =1A, I _B =4mA			2.0	V

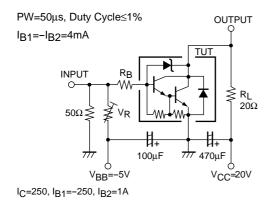
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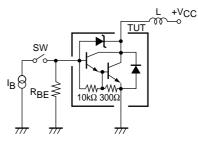
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Inductive Load Handling Capability	Es/b	L=100mH, R _{BE} =100Ω	25			mJ
Collector-to-Base Breakdown Voltage	V _(BR) CBO	I _C =100μA, I _E =0	50	60	70	V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =1mA, R _{BE} =∞	50	60	70	V
Turn-on Time	ton	See specified Test Circuit.		0.2		μs
Storage Time	t _{stg}	See specified Test Circuit.		3.5		μs
Fall Time	t _f	See specified Test Circuit.		0.5		μs

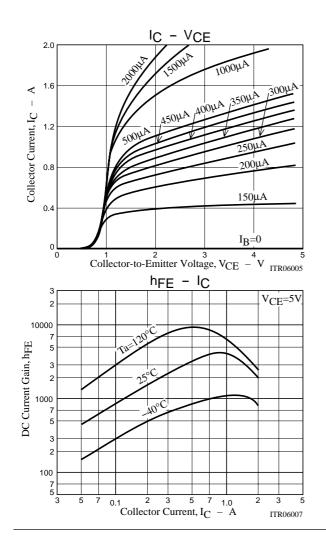
Switching Time Test Circuit

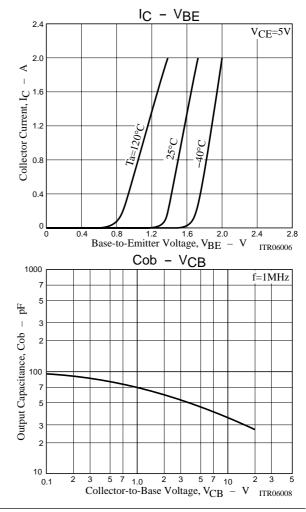


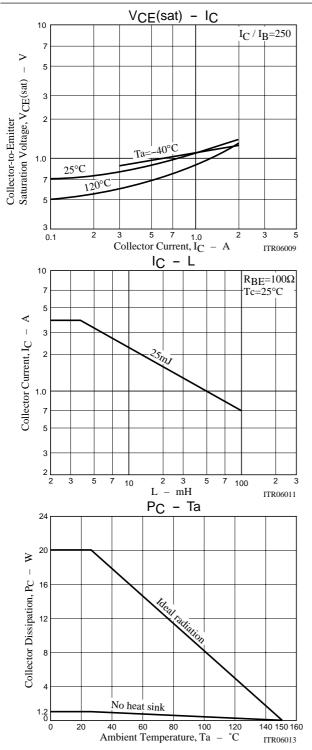
Es/b Test Circuit

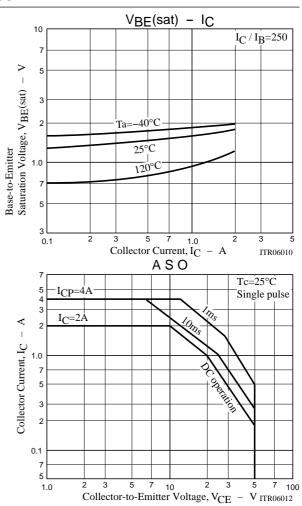












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